

# Adam Adikimenakis

## *Personal Details*

Born in Heraklion, Greece 19 April 1978

Marital status: Married, 2 children

email: adam@physics.uoc.gr

## *Current Employment*

1. Post Doctoral Researcher with Microelectronics Research Group (MRG) / Institute of Electronic Structure and Laser (IESL) / Foundation for Research and Technology Hellas (FORTH)
2. Visiting Instructor at Physics Department, University of Crete, Greece

## *Work Experience*

1. 12/2016 – [To date]: Research associate at IESL/FORTH
2. 10/2015-11/2016: Research associate at University of Crete
3. 02/2010-09/2015: Research associate at IESL/FORTH
4. 2003-2009: Research assistant at IESL/FORTH (MSc & PhD)

## *Teaching Experience*

**Teaching as visiting instructor** of the following courses:

1. “Semiconductor Physics Lab” 3 Semesters- Post Graduate Level, Physics dept University of Crete (2016-2019)
2. “Physics of Semiconductor Devices (Lab)” 2 Semesters – Undergraduate Level, Physics dept University of Crete (2016-2018)
3. “Physics Laboratory 1” 2 Semesters – Undergraduate Level, Technical Institute of Crete (2010-2013)

**Teaching assistant** in physics labs, Physics department, University of Crete, Greece (1999-2008)

## *Education*

**Doctor of Philosophy** (2009), Physics department, University of Crete (GR)

**Master of Science** (2004), Physics department, University of Crete (GR)

**Bachelor of Science** (2001), Physics, University of Crete (GR)

## *Languages*

1. **English:** First Certificate in English, University of Cambridge (grade B)
2. **French:** Basic user

## *Research Interests*

1. III-Nitride wide band gap semiconductors
2. Molecular Beam Epitaxy growth of III-Nitrides
3. III-nitride based Heterostructures and Nanostructures for Electronic and Optoelectronic applications

## *Participation in Projects as Member of the Research Team*

### **European Commission funded projects**

1. IST-FET UltraGaN - InAlN/(In)GaN Heterostructure Technology for Ultra-high Power Microwave Transistor
2. FP7 NMP MorGaN - Materials for Robust Gallium Nitride

### **National Research Projects**

- 1) PENED 01ΕΔ583 - Ανάπτυξη προηγμένων υλικών και διατάξεων με βάση τον νέο ημιαγωγό νιτρίδιο του γαλλίου (GaN) για μικροκυματικές εφαρμογές
- 2) ARISTEIA-NITROHEMT - Novel AlN and InN nano-heterostructures for high electron mobility transistors
- 3) NanoWire-THALES - Spontaneous growth, properties and devices of III-V semiconductor nanowires

### **Alternative funding agencies**

- 1) FP7-REGPOT-2012-2013-1 CCQCN - Crete Center For Quantum Complexity And Nanotechnology

## *Publications*

1. Publications in peer reviewed journals: 42
2. Citations (Scopus): 452
3. h-index (Scopus): 13

## *Journal Reviewer*

1. Journal of Crystal Growth
2. Solid State Electronics
3. Journal of Applied Physics
4. Materials Science in Semiconductor Processing

### *Supervision of Graduate Students*

1. Member of the committee for the bachelor thesis of two students, Physics department, university of Crete, Greece (2016-2017)

### *Distinctions*

1. “GaN heterostructures with diamond and graphene” B. Pécz, L. Tóth, G. Tsiakatouras, A. Adikimenakis, A. Kovács, M. Duchamp, R. E. Dunin-Borkowski, R. Yakimova, P. L. Neumann, H. Behmenburg, B. Foltynski, C. Giesen, M. Heuken, and A. Georgakilas, *Semicond. Sci. Technol.* 30, 114001 (2015). **Selected by the Editorial Board of Semiconductor Science and Technology to be included in the 2015 Article Highlights collection.**

### *Scientific Event Organization*

1. 19<sup>th</sup> HETECH conference (2010), Crete, Greece (Member of the organizing committee)
2. 12<sup>o</sup> EXMATEC conference (2014), Delfi, Greece (Member of the organizing committee)